

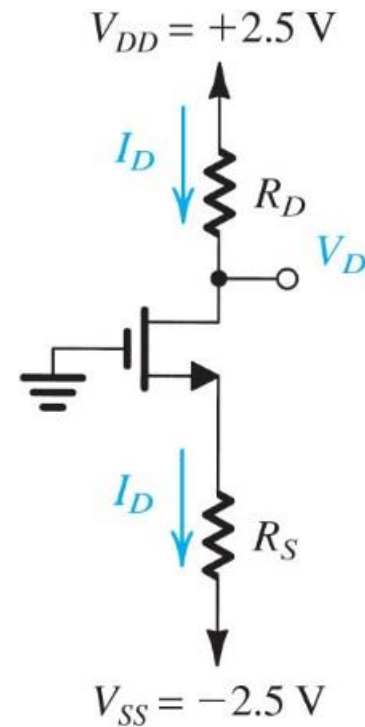
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# MOSFET at DC

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# Exercise

- Design the circuit in the figure to have  $I_D = 0.3 \text{ mA}$  and  $V_D = 0.3 \text{ V}$ .
- Assume
  - $V_T = 0.5 \text{ V}$
  - $\mu_n C_{ox} = 400 \mu\text{A V}^{-2}$
  - $L = 0.4 \mu\text{m}$
  - $W = 5 \mu\text{m}$



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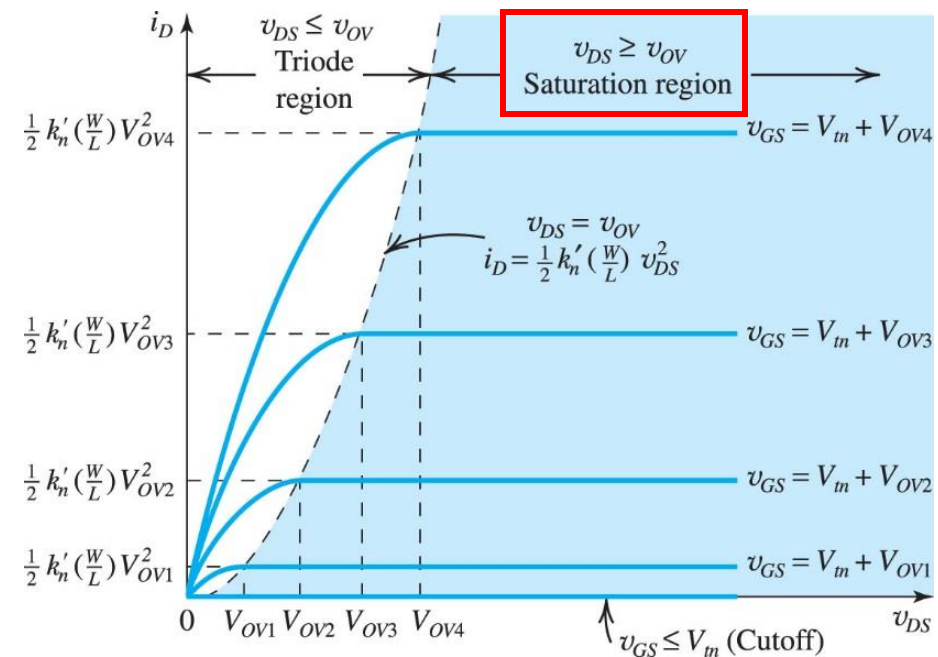
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# MOSFET as amplifier

# MOSFET as amplifier

- Transistors can be used as switches and as **amplifier**, depending in which region of their IV characteristic they are operated in
- To use a MOSFET as an amplifier, it has to be operated in **saturation** where it behaves as a **voltage controlled current source**

$$i_D = \frac{1}{2} (\mu_n C_{OX}) \left( \frac{W}{L} \right) (v_{GS} - V_t)^2$$

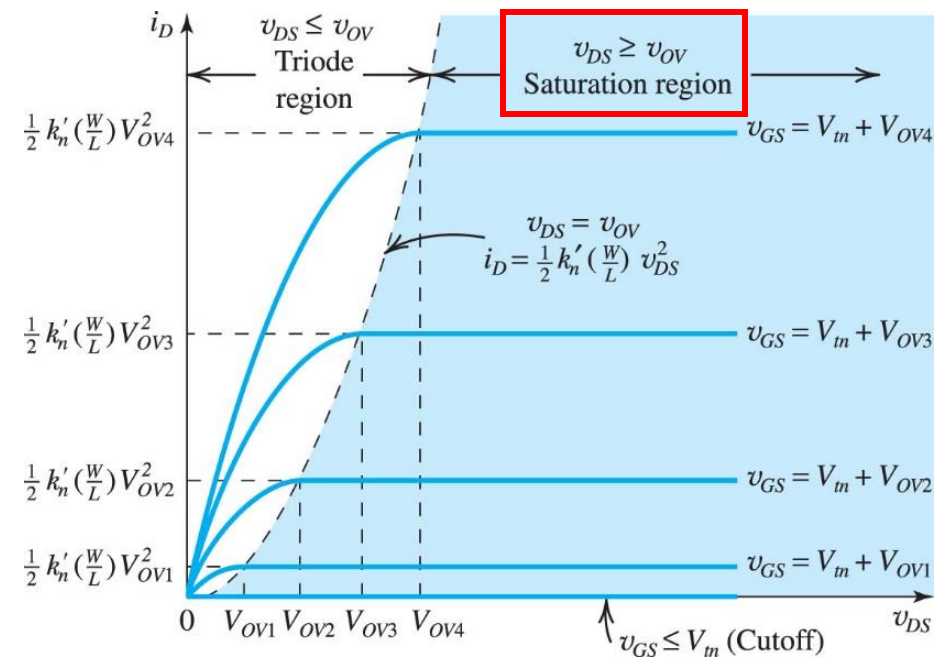


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# MOSFET as amplifier

- MOSFET in saturation
  - The voltage between gate and source,  $v_{GS}$ , controls the drain current,  $i_D$
- In first approximation, ignoring the channel length modulation effect,  $i_D$  in saturation does not depend on  $v_{DS}$  because the channel is pinched off at the drain end

$$i_D = \frac{1}{2} (\mu_n C_{OX}) \left( \frac{W}{L} \right) (v_{GS} - V_t)^2$$



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# MOSFET as amplifier

- For the transistor to work in saturation  $v_{DS} \geq v_{OV}$ 
  - This implies that that  $v_{GD} \leq V_t$
  - No charge left at drain end  $\rightarrow$  the channel is pinched off
- How do we design a linear amplifier using such a non-linear device?  $\rightarrow$  **Bias and small signal model**

## Saturation Region

Pinched-off channel, obtained by:

$$v_{GD} \leq V_{in}$$

or equivalently:

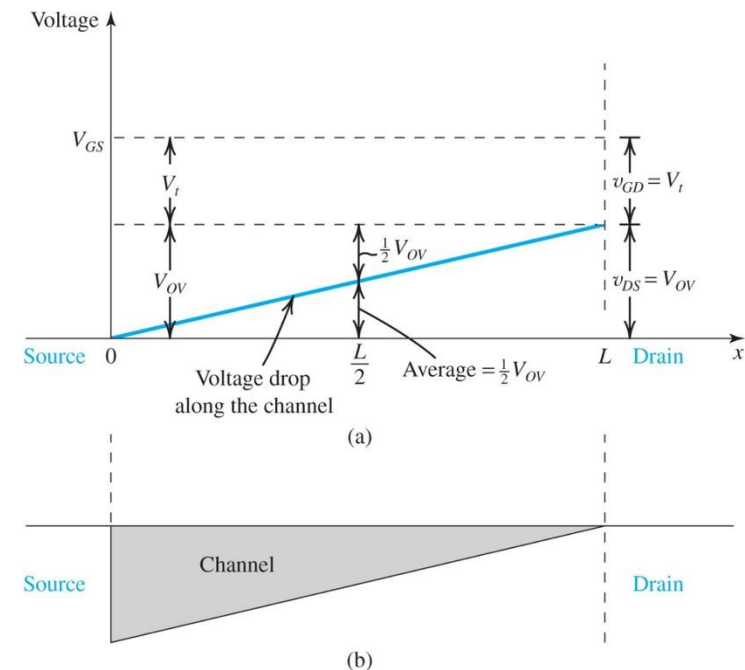
$$v_{DS} \geq v_{OV}$$

Then

$$i_D = \frac{1}{2} k'_n \left( \frac{W}{L} \right) (v_{GS} - V_{in})^2$$

or equivalently,

$$i_D = \frac{1}{2} k'_n \left( \frac{W}{L} \right) v_{OV}^2$$



# Voltage amplifier

- The MOSFET is a **transconductance amplifier**, i.e. an amplifier whose input signal is a voltage and whose output signal is a current

Type	Circuit Model	Gain Parameter	Ideal Characteristics
Voltage Amplifier		Open-Circuit Voltage Gain $A_{vo} \equiv \frac{v_o}{v_i} \Big _{i_o=0} \text{ (V/V)}$	$R_i = \infty$ $R_o = 0$
Current Amplifier		Short-Circuit Current Gain $A_{is} \equiv \frac{i_o}{i_i} \Big _{v_o=0} \text{ (A/A)}$	$R_i = 0$ $R_o = \infty$
Transconductance Amplifier		Short-Circuit Transconductance $G_m \equiv \frac{i_o}{v_i} \Big _{v_o=0} \text{ (A/V)}$	$R_i = \infty$ $R_o = \infty$
Transresistance Amplifier		Open-Circuit Transresistance $R_m \equiv \frac{v_o}{i_i} \Big _{i_o=0} \text{ (V/A)}$	$R_i = 0$ $R_o = 0$

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# Voltage amplifier

- To obtain a voltage amplifier, make  $i_D$  flow into a resistor

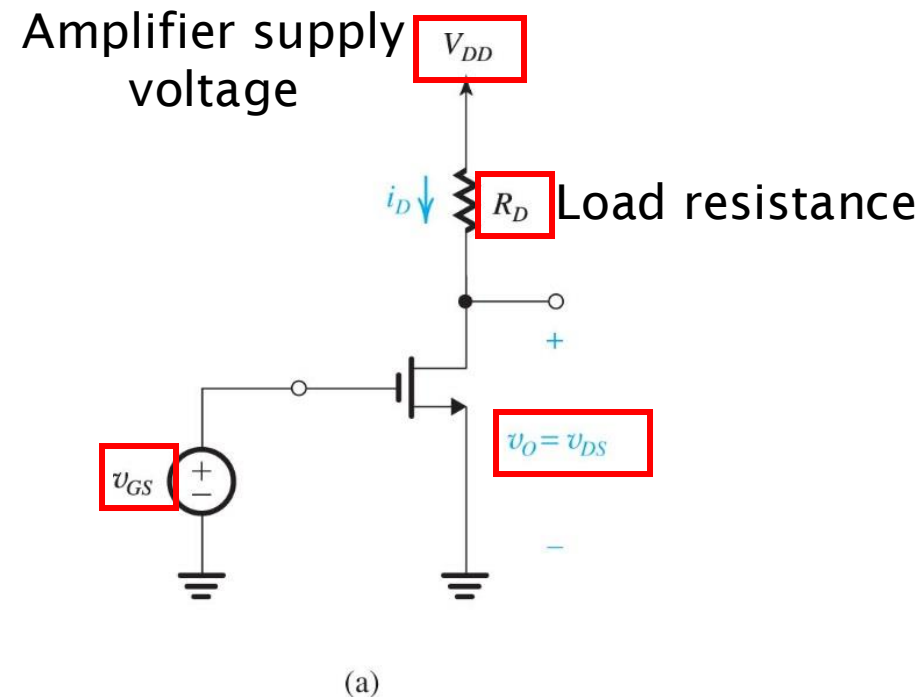
## Common source configuration

Input voltage

$$v_{GS} = V_{GS} + v_{gs}$$

DC bias

Signal



Output voltage

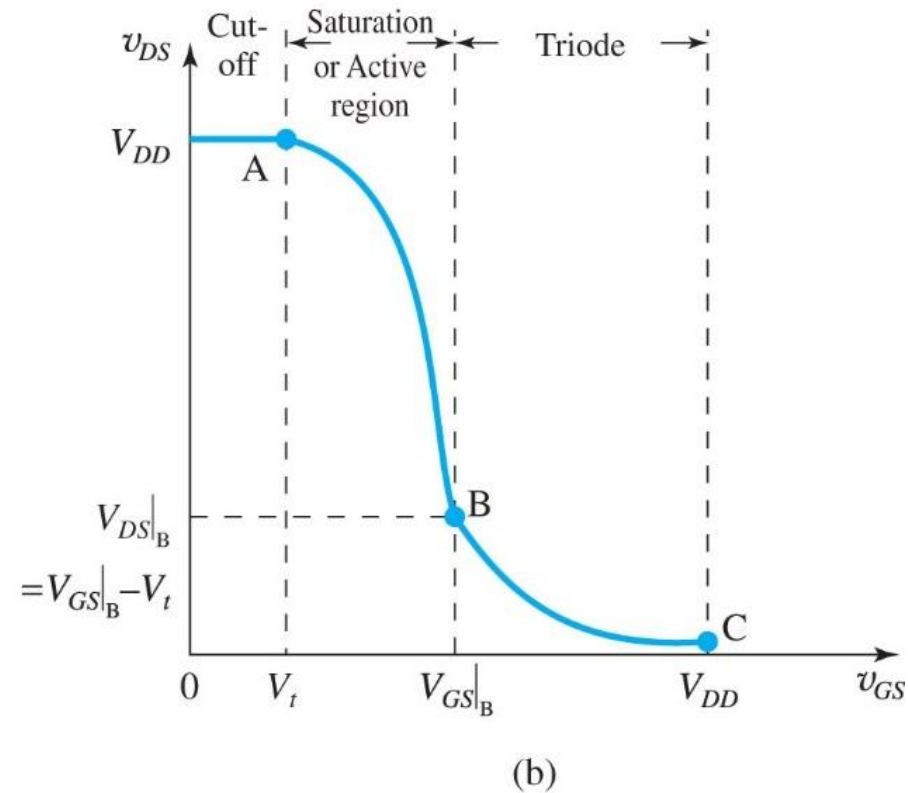
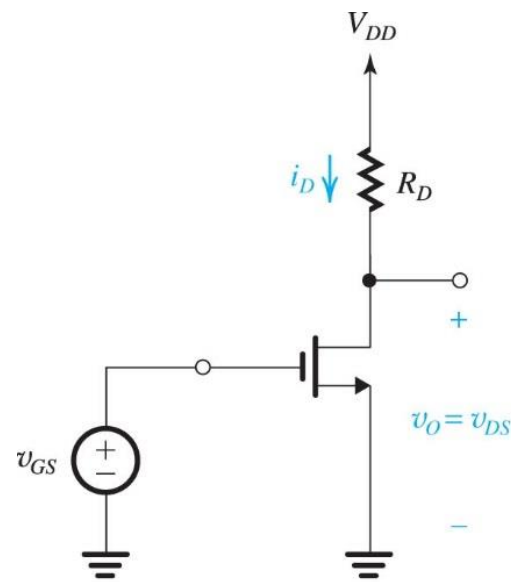
$$v_O = v_{DS} = V_{DD} - i_D R_D = V_{DD} - \frac{1}{2} k_n (v_{GS} - V_t)^2 R_D$$

$$[k_n = (\mu_n C_{ox})]$$



# Voltage amplifier

- The **voltage transfer characteristics** (VTC) plots output voltage vs input voltage



Output voltage

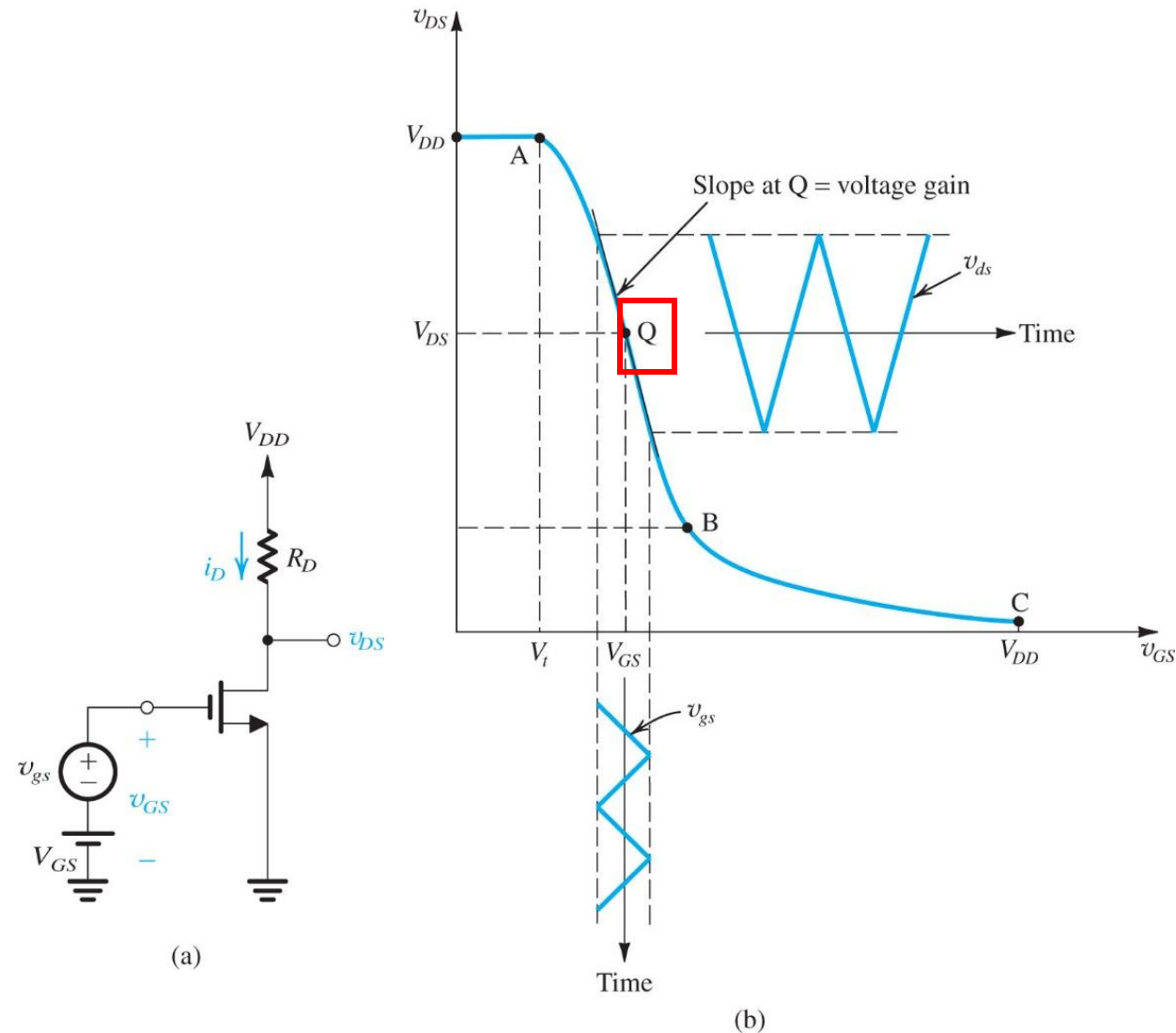
$$v_O = v_{DS} = V_{DD} - i_D R_D = V_{DD} - \frac{1}{2} k_n (v_{GS} - V_t)^2 R_D$$

# Obtaining linear amplification

- Let's first consider the **DC component of the input signal,  $V_{GS}$**
- This is chosen to select operation at a **point Q** in the saturation region of the VTC
- Q is known as bias point/dc operating **point/quiescent point**
- This  $V_{GS}$  defines

$$V_{DS} = V_{DD} - \frac{1}{2} k_n (V_{GS} - V_t)^2 R_D$$

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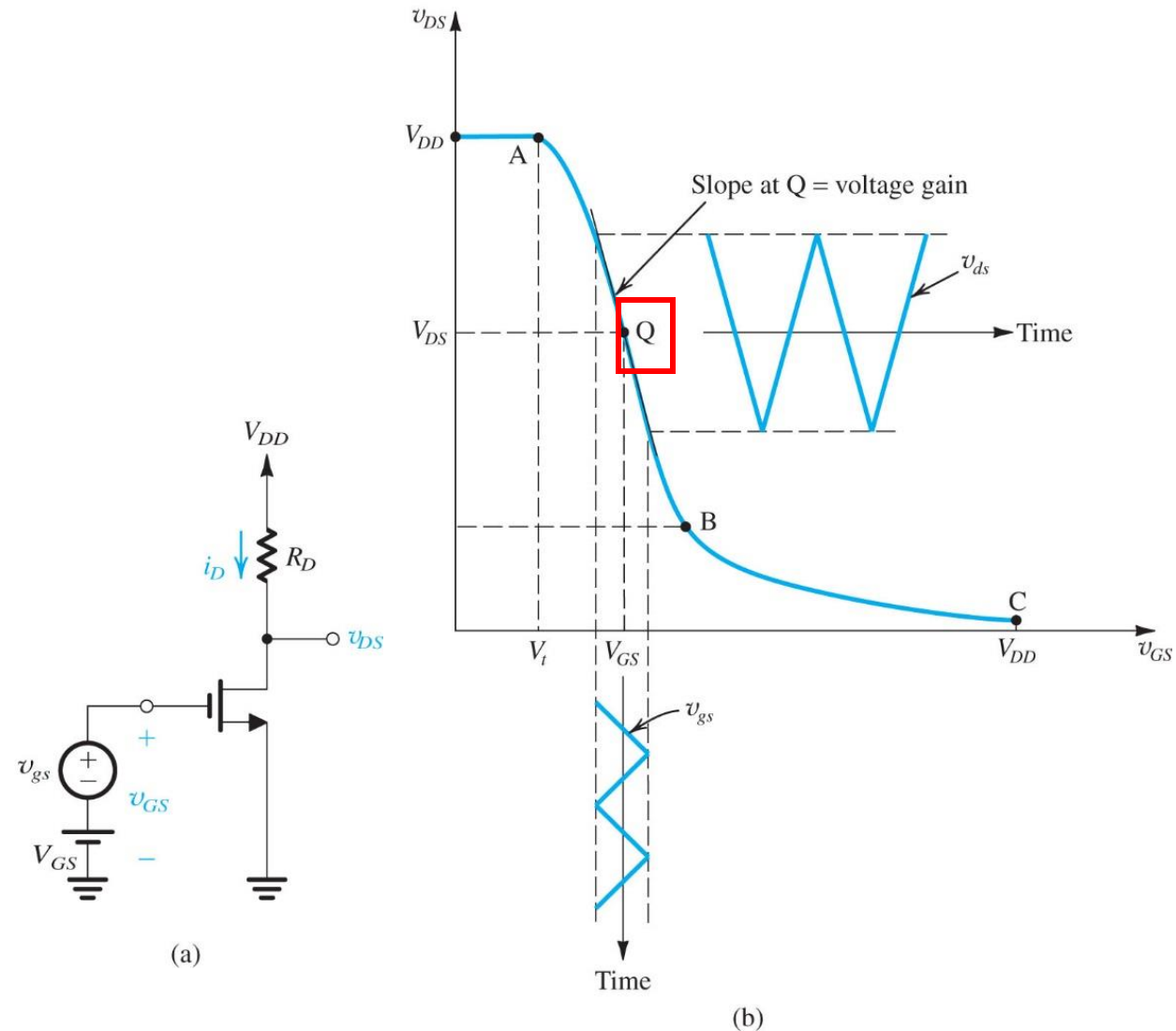


# Obtaining linear amplification

- Now let's apply an **input signal,  $v_{gs}$** , that is superimposed on the DC bias,  $V_{GS}$

$$v_{DS} = V_{DD} - \frac{1}{2} k_n R_D (V_{GS} + v_{gs} - V_t)^2$$

- As long as  **$v_{gs}$  is small**, the excursion of the instantaneous operation point is restricted to a small, almost linear portion of the VTC around Q → The output  **$v_{DS}$  is a linear function of the input**
- The smaller the signal,  $v_{gs}$ , the greater the linearity



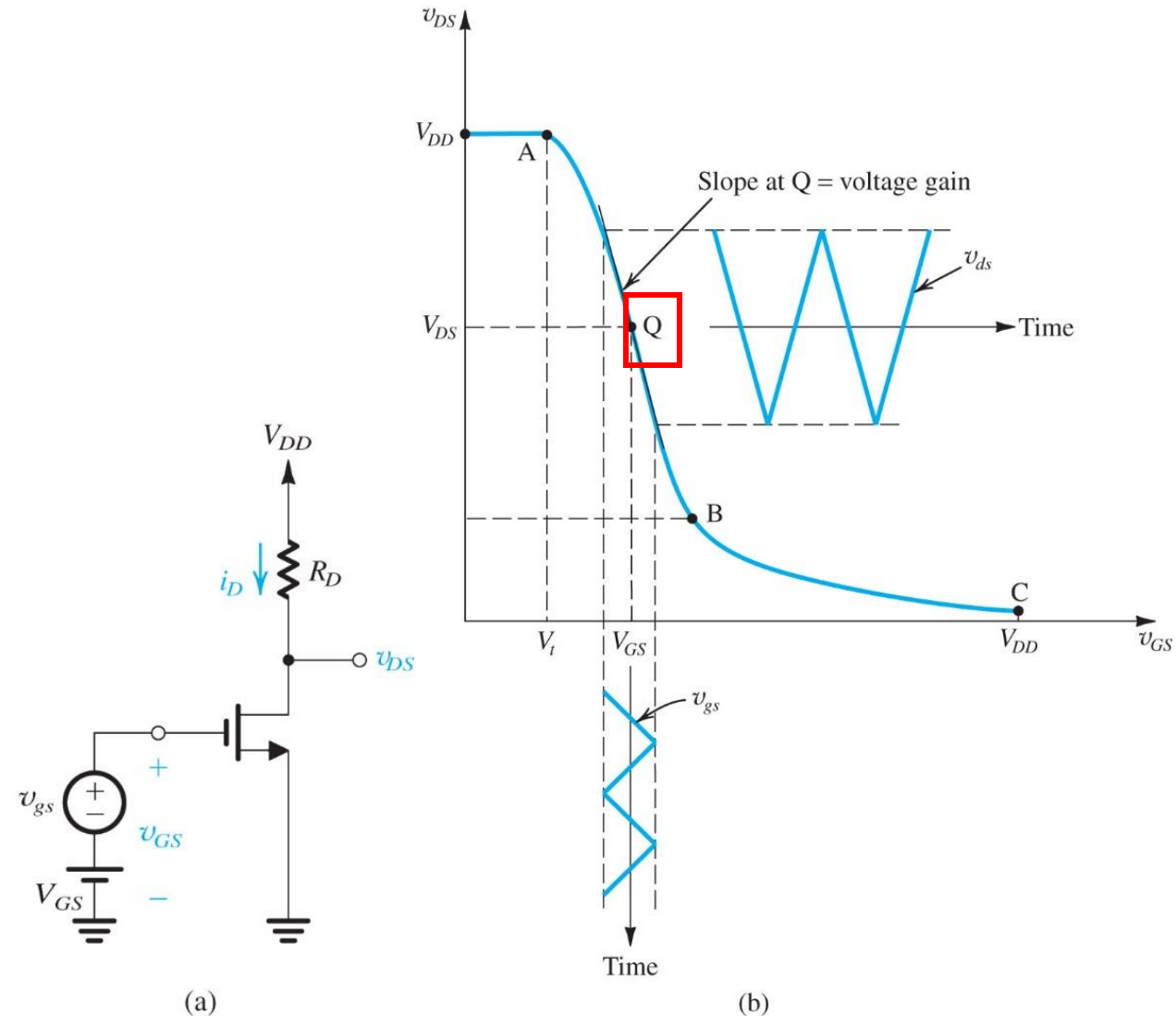
# The small-signal voltage gain

- The gain of the amplifier is the slope of the VTC at the bias point Q, i.e.

$$v_{GS} = V_{GS}$$

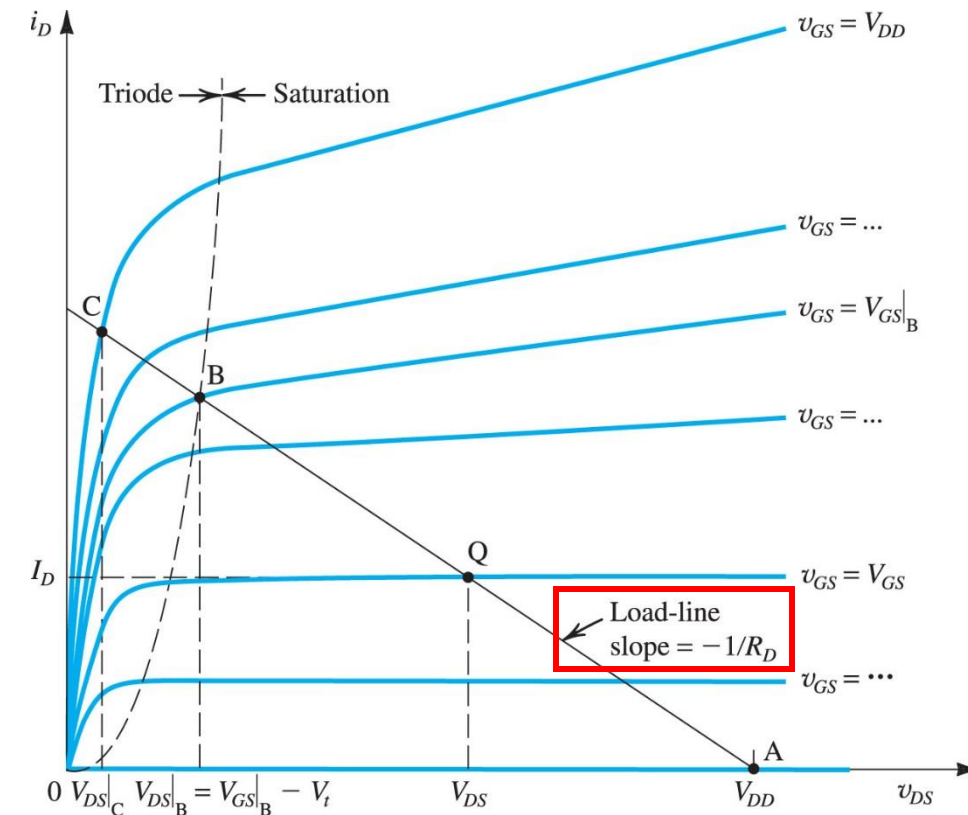
$$A_v = \frac{dv_{DS}}{dv_{GS}} = -k_n(V_{GS} - V_t)R_D = -k_nV_{OV}R_D$$

- Negative gain = there is a 180° phase shift between input and output → this amplifier is **inverting**



# Fixing the bias point Q

- Q needs to be chosen to **maximise the allowable output signal swing and the gain**
- Q can be obtained graphically as the point where the VTC curve for a certain  $v_{GS}$  intersects the load line
- Load line equation:  $i_D = \frac{1}{R_D} (V_{DD} - v_{DS})$



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